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Datasheet of DG9232DQ-T1-E3 - IC SWITCH DUAL SPST 8MSOP

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DG9232, DG9233

Vishay Siliconix

Low-Voltage Dual SPST Analog Switch

DESCRIPTION

The DG9232, 9233 is a single-pole/single-throw monolithic CMOS analog device designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 35 ns, t_{OFF} : 20 ns), low on-resistance ($R_{DS(on)}$: 20 Ω) and small physical size, the DG9232, 9233 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9232, 9233 is built on Vishay Siliconix's low voltage BCD-15 process. Minimum ESD protection, per method 3015.7 is 2000 V. An epitaxial layer prevents latchup. Break-before -make is guaranteed for DG9232. 9233.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

BENEFITS

- Reduced power consumption
- Simple logic interface
- High accuracy
- Reduce board space

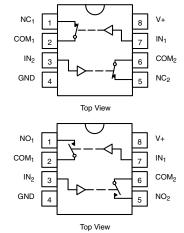
FEATURES

- Low voltage operation (+ 2.7 V to + 5 V)
- Low on-resistance R_{DS} (on): 20 Ω
- Fast switching t_{ON}: 35 ns, t_{OFF}: 20 ns
- Low leakage I_{COM(on)}: 200 pA max.
- Low charge injection Q_{INJ}: 1 pC
- Low power consumption
- TTL/CMOS compatible
- ESD protection > 2000 V (method 3015.7)
- Available in MSOP-8 and SOIC-8
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Battery operated systems
- Portable test equipment
- Sample and hold circuits
- Cellular phones
- Communication systems
- Military radio
- PBX, PABX guidance and control systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



| TRUTH TABLE - DG9232 | | | | |
|----------------------|--------|--|--|--|
| Logic | Switch | | | |
| 0 | On | | | |
| 1 | Off | | | |

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

| TRUTH TABLE - DG9233 | | | | |
|----------------------|--------|--|--|--|
| Logic | Switch | | | |
| 0 | Off | | | |
| 1 | On | | | |

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

| RDERING INFORMATION | | | | |
|---------------------|---------------|----------------|--|--|
| Temp Range | Package | Part Number | | |
| | | DG9232DY | | |
| | | DG9232DY-E3 | | |
| | SOIC-8 MSOP-8 | DG9232DY-T1 | | |
| | | DG9232DY-T1-E3 | | |
| - 40 °C to 85 °C | | DG9233DY | | |
| - 40 C to 65 C | | DG9233DY-E3 | | |
| | | DG9233DY-T1 | | |
| | | DG9233DY-T1-E3 | | |
| | | DG9232DQ-T1-E3 | | |
| | M3OF-8 | DG9233DQ-T1-E3 | | |

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

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| ABSOLUTE MAXIMUM RATINGS | | | | | |
|---|-------------------------------------|-------------|------|--|--|
| Parameter | | Limit | Unit | | |
| Reference V+ to GND | - 0.3 to + 13 | | | | |
| IN, COM, NC, NO ^a | - 0.3 to (V+ + 0.3) | V | | | |
| Continuous Current (Any terminal) | ± 20 | mA | | | |
| Peak Current (Pulsed at 1 ms, 10 % duty cycle | ± 40 | IIIA | | | |
| ESD (Method 3015.7) | | > 2000 | V | | |
| Storage Temperature | D suffix | - 65 to 125 | °C | | |
| Power Dissipation (Packages) ^b | 8-pin narrow body SOIC ^c | 400 | mW | | |

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 6.5 mW/°C above 70 °C.

| SPECIFICATIONS (V+ = 3 V) | | | | | | | |
|---|--------------------------------------|--|--------------|------------------|------------------|--------------|------|
| | | Test Conditions | | D Suffix | | | |
| | | Otherwise Unless Specified | | | - 40 °C to 85 °C | | |
| Parameter | Symbol | $V+ = 3 V, \pm 10 \%, V_{IN} = 0.8 V \text{ or } 2.4 V^{e}$ | Temp.a | Min.c | Typ.b | Max.c | Unit |
| Analog Switch | | | | | | | |
| Analog Signal Range ^d | V _{ANALOG} | | Full | 0 | | 3 | V |
| Drain-Source On-Resistance | R _{DS(on)} | V_{NO} or $V_{NC} = 1.5 \text{ V}$, V+ = 2.7 V $I_{COM} = 5 \text{ mA}$ | Room Full | | 30 | 50 80 | |
| R _{DS(on)} Match ^d | $\Delta R_{DS(on)}$ | V_{NO} or $V_{NC} = 1.5 \text{ V}$ | Room | | 0.4 | 2 | Ω |
| R _{DS(on)} Flatness ^d | R _{DS(on)} Flatness | V _{NO} or V _{NC} = 1 and 2 V | Room | | 4 | 8 | |
| NO or NC Off Leakage Current ^g | I _{NO/NC(off)} | V_{NO} or V_{NC} = 1 V/2 V, V_{COM} = 2 V/1 V | Room Full | - 100 - 5000 | 5 | 100 5000 | |
| COM Off Leakage Current ^g | I _{COM(off)} | $V_{COM} = 1 \text{ V/2 V}, V_{NO} \text{ or } V_{NC} = 2 \text{ V/1 V}$ | Room Full | - 100 - 5000 | 5 | 100 5000 | pА |
| Channel-On Leakage Current ^g | I _{COM(on)} | $V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/2 V}$ | Room Full | - 200 - 10000 | 10 | 200 10000 | |
| Digital Control | | | | | | | |
| Input Current | I _{INL} or I _{INH} | | Full | | 1 | | μΑ |
| Dynamic Characteristics | | | | | | | |
| Turn-On Time | t _{ON} | V_{NO} or $V_{NC} = 1.5 \text{ V}$ | Room Full | | 50 | 120 200 | |
| Turn-Off Time | t _{OFF} | VNO OF VNC = 1.5 V | Room Full | | 20 | 50 120 | ns |
| Charge Injection ^d | Q_{INJ} | $C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$ | Room | | 1 | 5 | рC |
| Off-Isolation | OIRR | $R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$ | Room | | - 74 | | dB |
| Crosstalk | X _{TALK} | 11[= 30 s2, 0[= 3 p1, 1 = 1 Wi12 | Room | | - 90 | | uБ |
| NC and NO Capacitance | C _{S(off)} | | Room | | 7 | | |
| Channel-On Capacitance | C _{COM(on)} | f = 1 MHz | Room | | 20 | | pF |
| COM-Off Capacitance | C _{COM(off)} | | Room | | 13 | | |
| Power Supply | | | | | | | |
| Positive Supply Range | V+ | | | 2.7 | | 12 | ٧ |
| Power Supply Current | I+ | $V+ = 3.3 \text{ V}, V_{IN} = 0 \text{ or } 3.3 \text{ V}$ | | | | 1 | μΑ |

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guaranteed by 5 V leakage tests, not production tested.

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| | | Test Conditions Otherwise Unless Specified | | D Suffix - 40 °C to 85°C | | | |
|---|--------------------------------------|--|--------------|-----------------------------|-------|--------------|-----|
| Parameter | Symbol | V+ = 5 V, \pm 10 %, V_{IN} = 0.8 V or 2.4 V^e | Temp.a | Min.c | Typ.b | Max.c | Uni |
| Analog Switch | | | | | | | |
| Analog Signal Range ^d | V _{ANALOG} | | Full | 0 | | 5 | V |
| Drain-Source On-Resistance | R _{DS(on)} | V_{NO} or $V_{NC} = 3.5 \text{ V}$, $V_{+} = 4.5 \text{ V}$ $I_{COM} = 5 \text{ mA}$ | Room Full | | 20 | 30 50 | |
| R _{DS(on)} Match ^d | $\Delta R_{DS(on)}$ | V_{NO} or $V_{NC} = 3.5 \text{ V}$ | Room | | 0.4 | 2 | Ω |
| R _{DS(on)} Flatness ^d | R _{DS(on)} Flatness | V_{NO} or $V_{NC} = 1$, 2 and 3 V | Room | | 2 | 6 | |
| NO or NC Off Leakage Current ^g | I _{NO/NC(off)} | V_{NO} or V_{NC} = 1 V/4 V, V_{COM} = 4 V/1 V | Room Full | - 100 - 5000 | 10 | 100 5000 | |
| COM Off Leakage Current | I _{COM(off)} | $V_{COM} = 1 \text{ V/4 V}, V_{NO} \text{ or } V_{NC} = 4 \text{ V/1 V}$ | Room Full | - 100 - 5000 | 10 | 100 5000 | рA |
| Channel-On Leakage Current | I _{COM(on)} | $V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/4 V}$ | Room Full | - 200 - 10000 | | 200 10000 | |
| Digital Control | | | | | | | |
| Input Current | I _{INL} or I _{INH} | | Full | | 1 | | μΑ |
| Dynamic Characteristics | | | | | | | |
| Turn-On Time | t _{ON} | V_{NO} or $V_{NC} = 3.0 \text{ V}$ | Room Full | | 35 | 75 150 | ns |
| Turn-Off Time | t _{OFF} | THO STANCE STOP | Room Full | | 20 | 50 100 | 113 |
| Charge Injection ^d | Q _{INJ} | $C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$ | Room | | 2 | 5 | рС |
| Off-Isolation | OIRR | $R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$ | Room | | - 74 | | dB |
| Crosstalk | X _{TALK} | | Room | | - 90 | | ub |
| NC and NO Capacitance | C _(off) | | Room | | 7 | | |
| Channel-On Capacitance | C _{D(on)} | f = 1 MHz | Room | | 20 | | pF |
| COM-Off Capacitance | C _{D(off)} | | Room | | 13 | | |
| Power Supply | | | | | | | |
| Positive Supply Range | V+ | | | 2.7 | | 12 | V |
| Power Supply Current | I+ | $V+ = 5.5 \text{ V}, V_{IN} = 0 \text{ or } 5.5 \text{ V}$ | | | | 1 | μΑ |

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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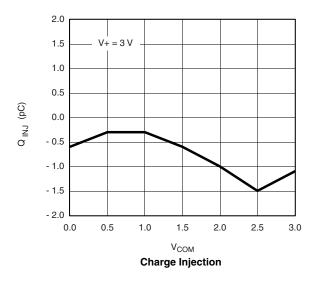


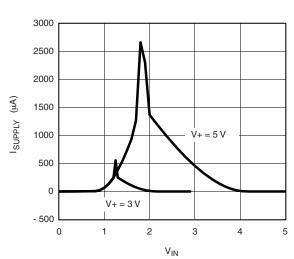
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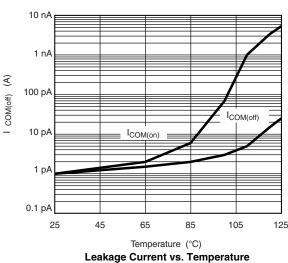
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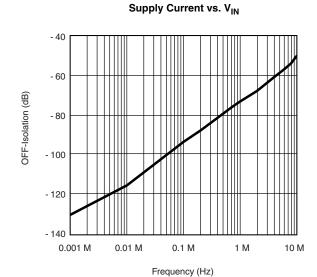
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

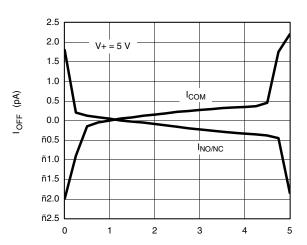






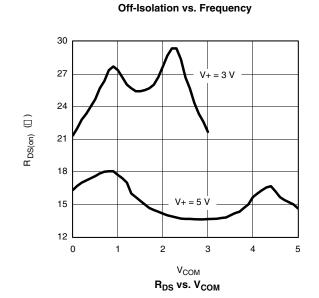






 V_{COM}

Off-Leakage vs. Voltage at 25 °C



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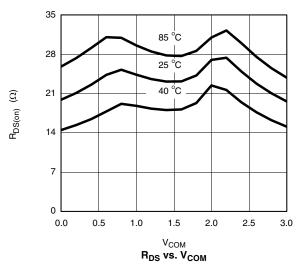


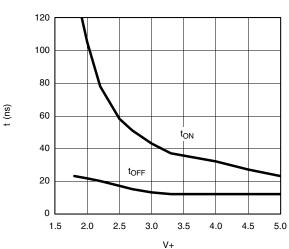


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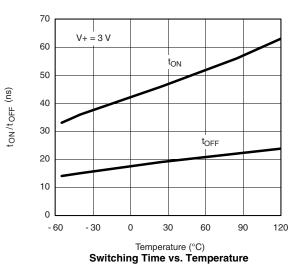
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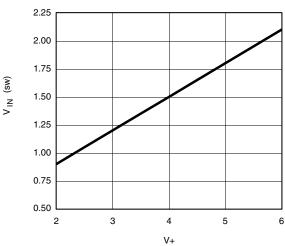
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted





 $t_{\mbox{ON/tOFF}}$ vs. Power Supply Voltage





Input Switching Point vs. Power Supply Voltage



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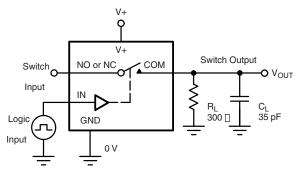
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TEST CIRCUITS



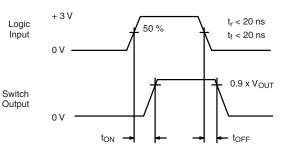
t_r < 5 ns

 $t_f < 5 \text{ ns}$



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

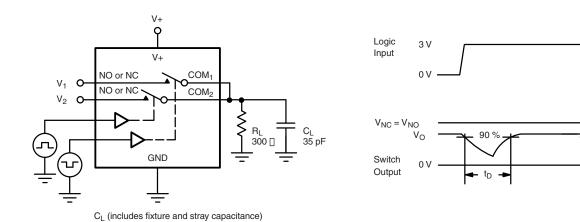
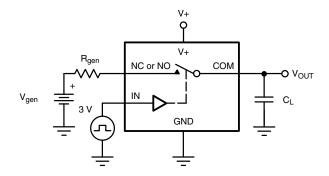
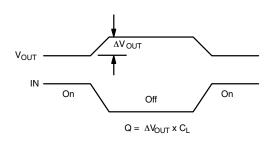


Figure 2. Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection





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TEST CIRCUITS

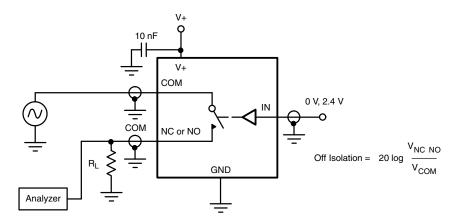


Figure 4. Off-Isolation

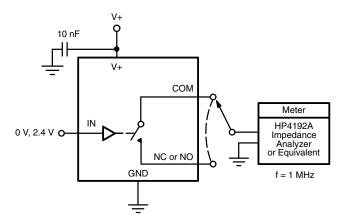


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?70837.

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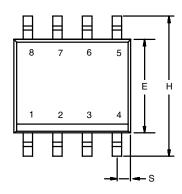


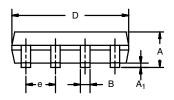


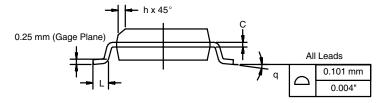
Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEADJEDEC Part Number: MS-012







| | MILLIMETERS INCHES | | | HES | |
|--------------------------------|--------------------|------|-----------|-------|--|
| DIM | Min | Max | Min | Max | |
| Α | 1.35 | 1.75 | 0.053 | 0.069 | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | |
| Е | 3.80 | 4.00 | 0.150 | 0.157 | |
| е | 1.27 | BSC | 0.050 BSC | | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | |
| q | 0° | 8° | 0° | 8° | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | |
| FCN: C-06527-Bev. I. 11-Sep-06 | | | | | |

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

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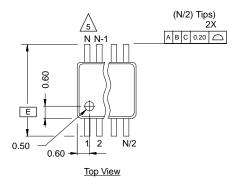
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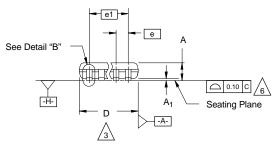


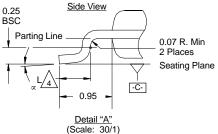
Package Information Vishay Siliconix

MSOP: 8-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)







NOTES:

- Die thickness allowable is 0.203 ± 0.0127 .
- Dimensioning and tolerances per ANSI.Y14.5M-1994.



Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane -H-, mold flash or protrusions shall not exceed



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



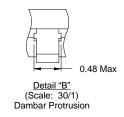
Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

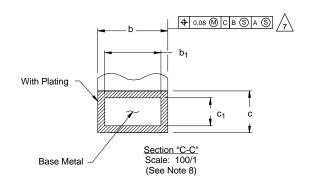
Controlling dimension: millimeters.

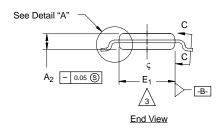
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

/11\ Datums -A- and -B- to be determined Datum plane -H-.

Exposed pad area in bottom side is the same as teh leadframe pad size.







N = 8L

| | МІ | | | | | |
|----------------|---|------------|------|------|--|--|
| Dim | Min | Nom | Max | Note | | |
| Α | - | - | 1.10 | | | |
| A ₁ | 0.05 | 0.10 | 0.15 | | | |
| A ₂ | 0.75 | 0.85 | 0.95 | | | |
| b | 0.25 | - | 0.38 | 8 | | |
| b ₁ | 0.25 | 0.30 | 0.33 | 8 | | |
| С | 0.13 | - | 0.23 | | | |
| c ₁ | 0.13 | 0.15 | 0.18 | | | |
| D | | 3.00 BSC | | | | |
| Е | | 4.90 BSC | | | | |
| E ₁ | 2.90 | 3.00 | 3.10 | 3 | | |
| е | | 0.65 BSC | | | | |
| e ₁ | | 1.95 BSC | | | | |
| L | 0.40 | 0.55 | 0.70 | 4 | | |
| N | 8 | | | 5 | | |
| œ | 0° | 4 ° | 6° | | | |
| | ECN: T-02080—Rev. C, 15-Jul-02 DWG: 5867 | | | | | |

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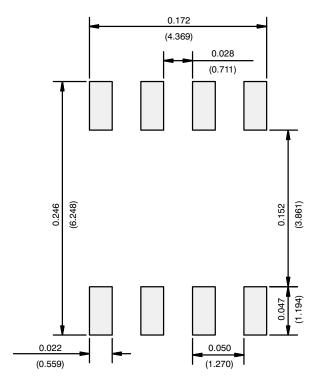


Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOT

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22 Revision: 21-Jan-08



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